TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# SM2LZ47

### AC POWER CONTROL APPLICATIONS

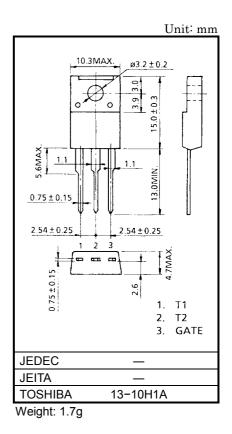
- Repetitive Peak Off-State Voltage : V<sub>DRM</sub> = 800V
  - R.M.S. On–State Current : I<sub>T</sub> (RMS) = 2A
- High Commutation (dv / dt)
- $(dv / dt) c = 5V / \mu s$  (Min.)
- :  $V_{ISOL} = 1500 V AC$

#### **MAXIMUM RATINGS**

• Isolation Voltage

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CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage	V <sub>DRM</sub>	800	V	
R.M.S. On-State Current (Full Sine Waveform)	I <sub>T (RMS)</sub>	2	А	
Peak One Cycle Surge On-State	ITSM	8 (50Hz)	А	
Current (Non-Repetitive)		8.8 (60Hz)	A	
I <sup>2</sup> t Limit Value	l <sup>2</sup> t	0.32	A <sup>2</sup> s	
Critical Rate of Rise of On-State Current (Note)	di / dt	50	Α / μs	
Peak Gate Power Dissipation	P <sub>GM</sub>	3	W	
Average Gate Power Dissipation	P <sub>G (AV)</sub>	0.3	W	
Peak Gate Voltage	V <sub>FGM</sub>	10	V	
Peak Gate Current	I <sub>GM</sub>	1.6	А	
Junction Temperature	Тj	-40~125	°C	
Storage Temperature Range	T <sub>stg</sub>	-40~125	°C	
Isolation Voltage (AC, t = 1min.)	VISOL	1500	V	



Note: di / dt test condition

 $V_{DRM}$  = 400V,  $I_{TM} \le 3A$ ,  $t_{gw} \ge 10\mu$ s,  $t_{gr} \le 250$ ns,  $i_{gp}$  =  $I_{GT} \times 2.0$ 

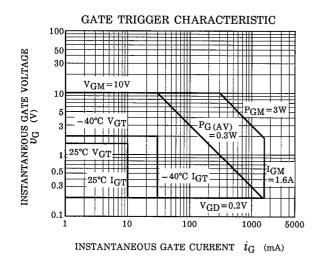
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

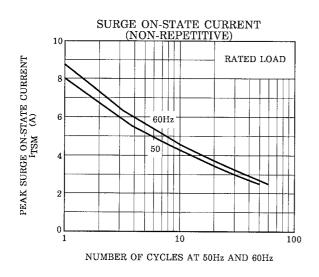
CHARACTERISTIC	CHARACTERISTIC SYMBOL TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak Off-State Current I <sub>DRM</sub> V <sub>DRM</sub> = 800V			_	_	20	μA		
Gate Trigger Voltage	Ι		V <sub>D</sub> = 12V, R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)		_	1.5	v
	П	V <sub>GT</sub>		T2 (+) , Gate (−)	_	_	1.5	
	Ш			T2 (-) , Gate (-)	_	_	1.5	
Gate Trigger Current	I		V <sub>D</sub> = 12V, R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)	_	_	10	mA
	П	I <sub>GT</sub>		T2 (+) , Gate (−)	_	_	10	
	Ш		-	T2 (-) , Gate (-)	_	_	10	
Peak On-State Voltage		V <sub>TM</sub>	I <sub>TM</sub> = 3A		_	_	2.0	V
Gate Non-Trigger Voltage		V <sub>GD</sub>	V <sub>D</sub> = 800V, Tc = 125°C		0.2	_	_	V
Holding Current		Ι <sub>Η</sub>	V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A		_	_	10	mA
Thermal Resistance		R <sub>th (j−a)</sub>	Junction to Ambient, AC			_	58	°C/W
Critical Rate of Rise of Off-State Voltage dv / dt		V <sub>DRM</sub> = 800V, T <sub>j</sub> = 125°C Exponential Rise		_	500	_	V / µs	
Critical Rate of Rise of Off-State Vo at Communication	oltage	(dv / dt) c	V <sub>DRM</sub> = 400V, T <sub>j</sub> = 125°C (di / dt) c = - 0.5A / ms		5	_	_	V / µs

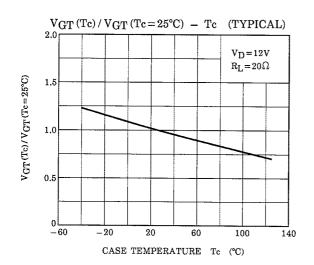
## MARKING

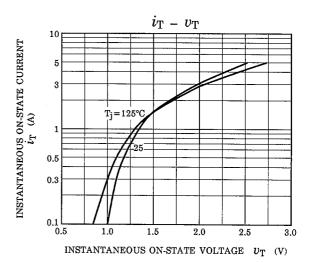
[<u>\*1</u>] [<u>\*2</u> [\*3

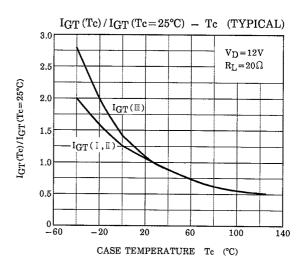
	NUMBER	SYMBOL		MARK	
]	*1	Toshiba Product Mar	K	5	
4	*2	TYPE	SM2LZ47	M2LZ47	
	*3	Lot Number Month (Starting from) Alphabet A Year (Last Decimal Digit of the Current Year )		Example 8A : January 1998 8B : February 1998 8L : December 1998	

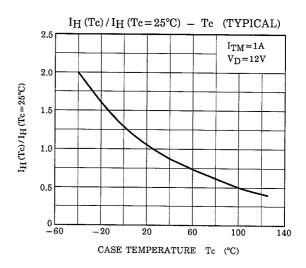




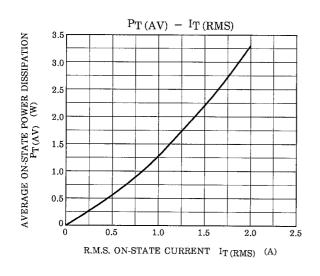


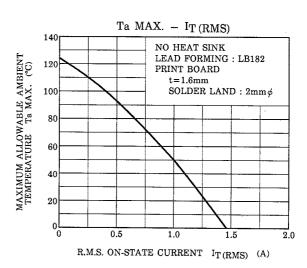




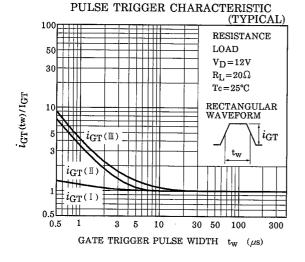


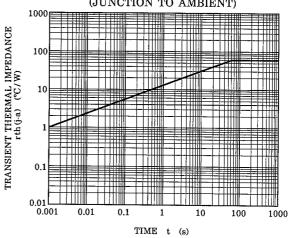
## TOSHIBA





TRANSIENT THERMAL IMPEDANCE (JUNCTION TO AMBIENT)





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